



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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If you have any questions related to this document, please contact our nearest sales office via e-mail or phone (details via salesaddresses@ween-semi.com).

Thank you for your cooperation and understanding,

WeEn Semiconductors

DATA SHEET

BT152B series Thyristors

Product specification

September 1997



Thyristors

BT152B series

GENERAL DESCRIPTION

Glass passivated thyristors in a plastic envelope suitable for surface mounting, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

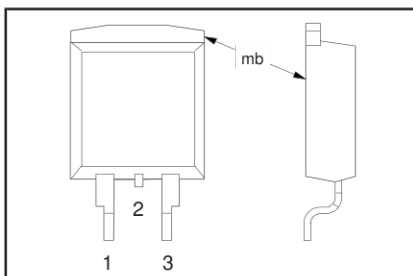
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	400R	600R	800R	V
V_{RRM}		450	650	800	
$I_{T(AV)}$	Average on-state current	13	13	13	A
$I_{T(RMS)}$	RMS on-state current	20	20	20	A
I_{TSM}	Non-repetitive peak on-state current	200	200	200	A

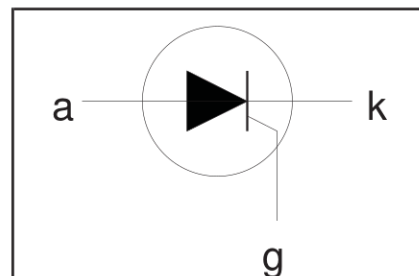
PINNING - SOT404

PIN	DESCRIPTION
1	cathode
2	anode
3	gate
mb	anode

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-400R 450 ¹	-600R 650 ¹	-800R 800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 103\text{ °C}$	-	13			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	20			A
I_{TSM}	Non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ °C}$ prior to surge	-	200			A
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	200			A
di_T/dt	Repetitive rate of rise of on-state current after triggering	$t = 8.3\text{ ms}$	-	220			A
		$t = 10\text{ ms}$	-	200			A ² s
I_{GM}	Peak gate current	$I_{TM} = 50\text{ A}$; $I_G = 0.2\text{ A}$;	-	5			A
V_{GM}	Peak gate voltage	$di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	5			V
V_{RGM}	Peak reverse gate voltage		-	5			V
P_{GM}	Peak gate power		-	20			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			°C
T_j	Operating junction temperature		-	125			°C

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

Thyristors

BT152B series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	minimum footprint, FR4 board	-	-	1.1	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	55	-	K/W

STATIC CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	3	32	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	25	80	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	15	60	mA
V_T	On-state voltage	$I_T = 40\text{ A}$	-	1.4	1.75	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.6	1.5	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}; I_T = 0.1\text{ A}; T_j = 125\text{ °C}$	0.25	0.4	-	V
		$V_D = V_{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125\text{ °C}$	-	0.2	1.0	mA

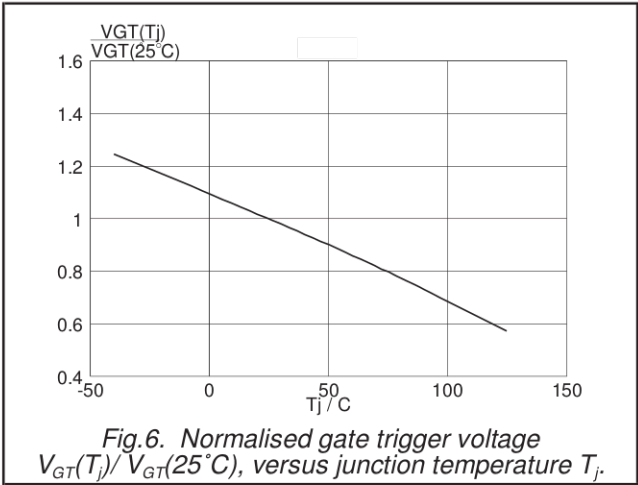
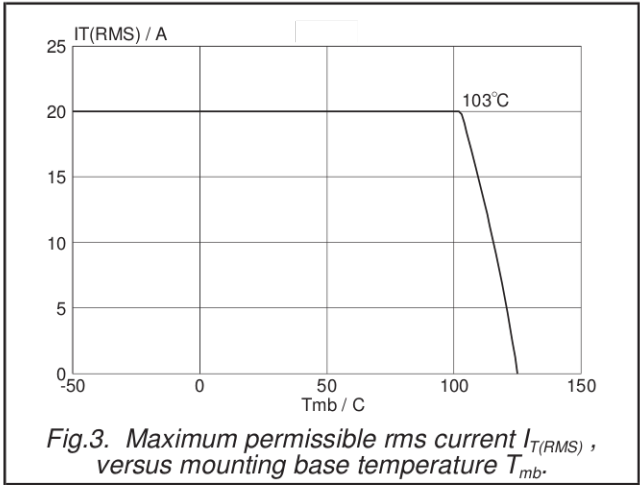
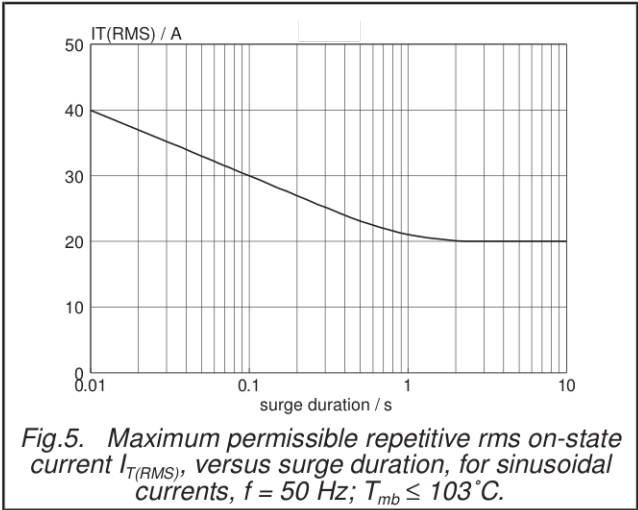
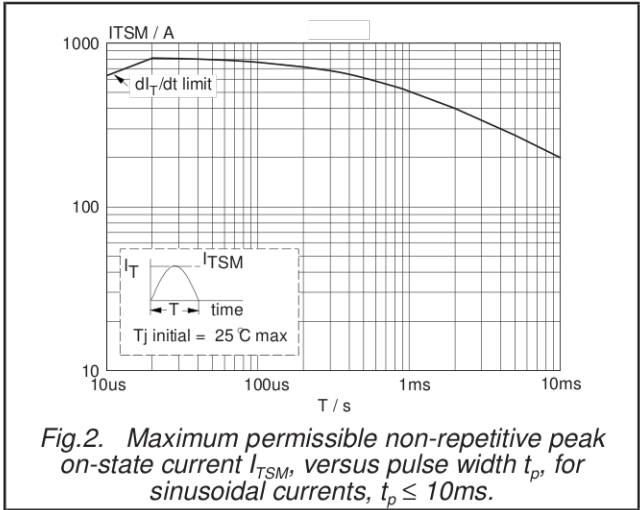
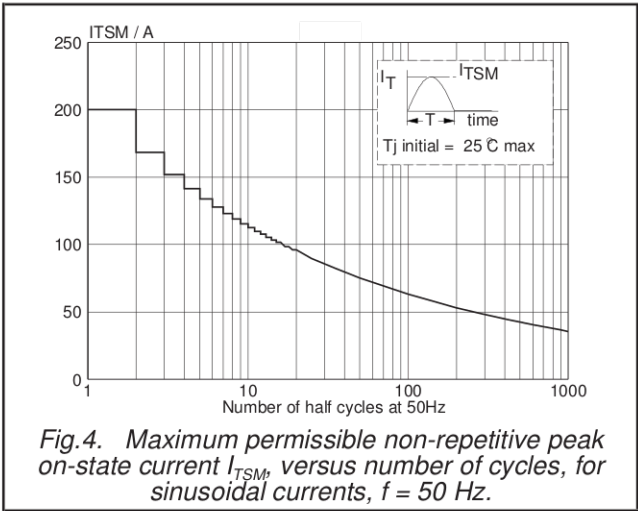
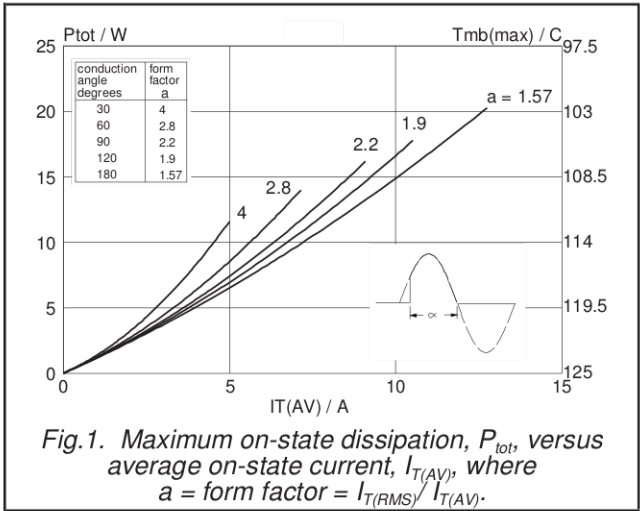
DYNAMIC CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform gate open circuit	200	300	-	V/ μ s
t_{gt}	Gate controlled turn-on time	$V_D = V_{DRM(max)}; I_G = 0.1\text{ A}; dI_G/dt = 5\text{ A}/\mu\text{s};$ $I_{TM} = 40\text{ A}$	-	2	-	μ s
t_q	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ $I_{TM} = 50\text{ A}; V_R = 25\text{ V}; dI_{TM}/dt = 30\text{ A}/\mu\text{s};$ $dV_D/dt = 50\text{ V}/\mu\text{s}; R_{GK} = 100\ \Omega$	-	70	-	μ s

Thyristors

BT152B series



Thyristors

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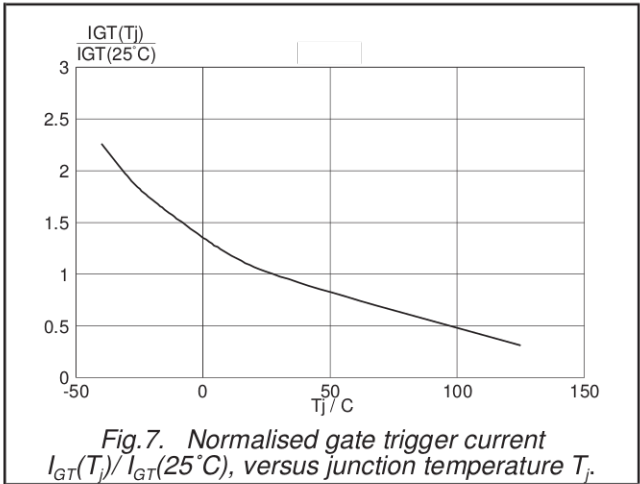


Fig. 7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^{\circ}\text{C})$, versus junction temperature T_j .

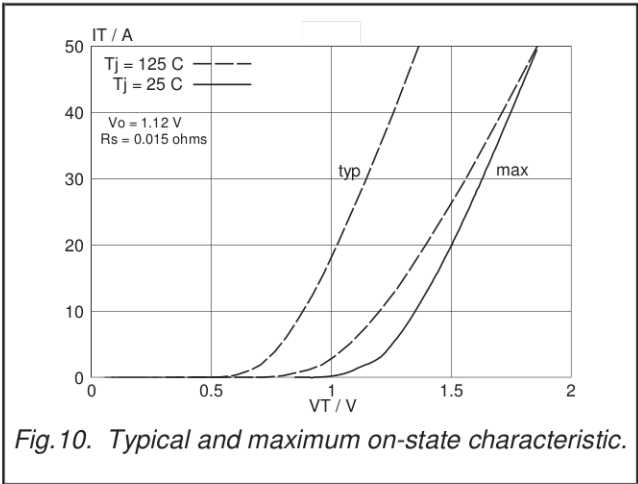


Fig. 10. Typical and maximum on-state characteristic.

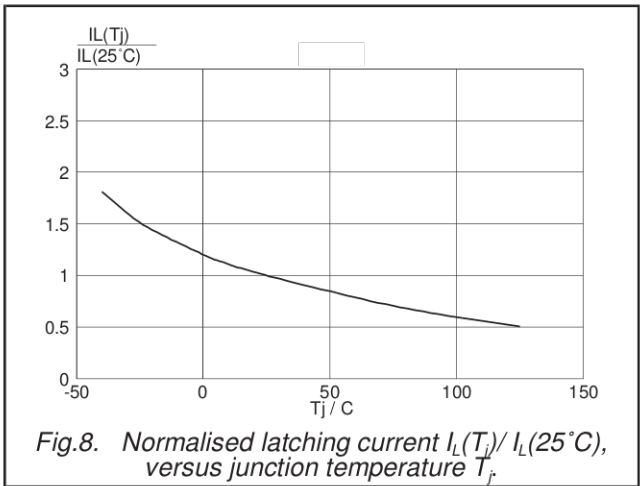


Fig. 8. Normalised latching current $I_L(T_j)/I_L(25^{\circ}\text{C})$, versus junction temperature T_j .

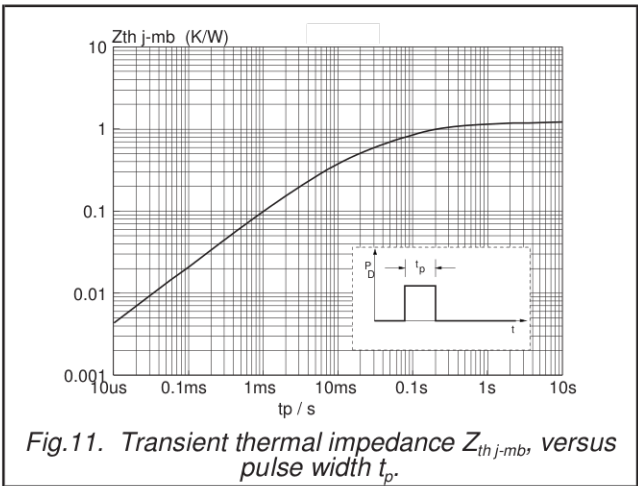


Fig. 11. Transient thermal impedance $Z_{th j-mb}$, versus pulse width t_p .

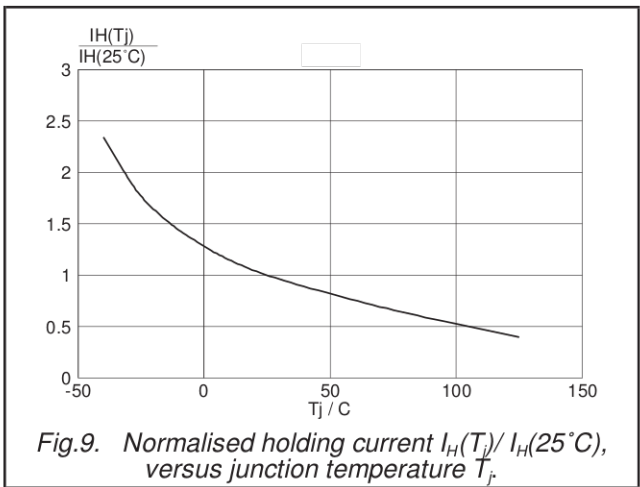


Fig. 9. Normalised holding current $I_H(T_j)/I_H(25^{\circ}\text{C})$, versus junction temperature T_j .

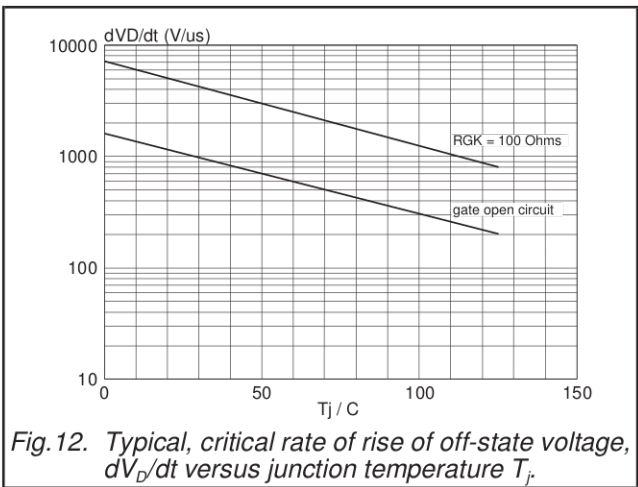
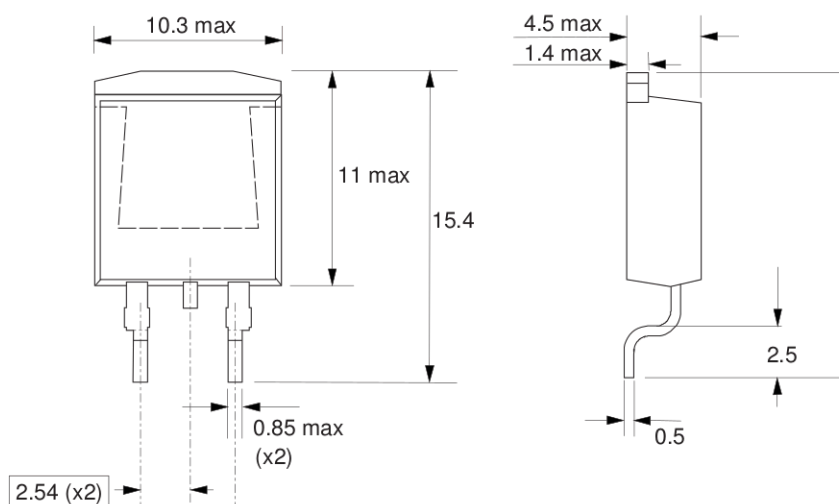


Fig. 12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j .

Thyristors

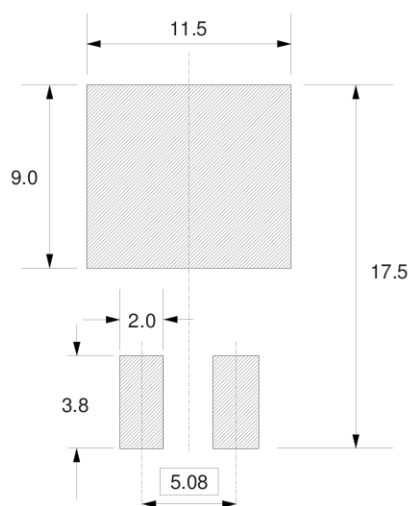
BT152B series

MECHANICAL DATA

*Dimensions in mm**Net Mass: 1.4 g**Fig.13. SOT404 : centre pin connected to mounting base.***Notes**

1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS

Dimensions in mm*Fig.14. SOT404 : minimum pad sizes for surface mounting.***Notes**

1. Plastic meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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